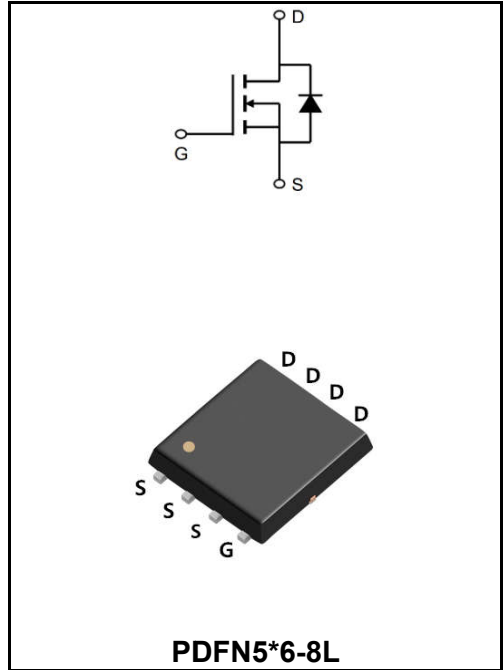


30V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	135A
V_{DSS}	30V
R_{DS(on)-typ(@V_{GS}=10V)}	< 1.6mΩ (Type:1.3 mΩ)



Application

- ◆ Lithium battery protection
- ◆ Wireless impact
- ◆ Mobile phone fast charging

Product Specification Classification

Part Number	Package	Marking	Pack
YFW135N03NF	PDFN5*6-8L	YFW 135N03NF XXXXX	5000PCS/Tape

Maximum Ratings at T_c=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	30	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current, V _{GS} @ 10V ^{1.6} @T _c =25°C	I_D	135	A
Continuous Drain Current, V _{GS} @ 10V ^{1.6} @T _c =100°C	I_D	97	A
Continuous Drain Current, V _{GS} @ 10V ¹ @T _A =25°C	I_D	31	A
Continuous Drain Current, V _{GS} @ 10V ¹ @T _A =70°C	I_D	25	A
Pulsed Drain Current ²	I_{DM}	350	A
Single Pulsed Avalanche Energy ³	E_{AS}	151	mJ
Avalanche Current	I_{AS}	55	A
Total Power Dissipation ⁴ @T _c =25°C	P_D	62.5	W
Total Power Dissipation ⁴ @T _A =25°C	P_D	2.5	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C
Thermal Resistance Junction-ambient ¹	R_{θJA}	50	°C/W
Thermal Resistance, Junction - Case ¹	R_{θJC}	2.0	°C/W

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	BV_{DSS}	30	-	-	V
Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=20A$	$R_{DS(ON)}$	-	1.3	1.6	mΩ
	$V_{GS}=4.5V, I_D=20A$		-	1.9	2.5	
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	1.2	1.6	2.2	V
Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ C$	I_{DSS}	-	-	1	μA
	$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ C$		-	-	5	
Gate -Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	I_{GSS}	-	-	±100	nA
Forward Transconductance	$V_{DS}=5V, I_D=20A$	g_{fs}	-	35	-	S
Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	R_g	-	1.0	-	Ω
Total Gate Charge(4.5V)	$V_{DS}=15V$ $I_D=20A$ $V_{GS}=10V$	Q_g	-	45	-	nC
Gate-Source Charge		Q_{gs}	-	9.8	-	
Gate-Drain Charge		Q_{gd}	-	6.5	-	
Turn-on delay time	$V_{DD}=15V$ $V_{GS}=10V$ $I_D=20A$ $R_G=3.3\Omega$	$t_{d(on)}$	-	10.3	-	ns
Rise Time		T_r	-	6.2	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	56	-	
Fall Time		t_f	-	8.4	-	
Input Capacitance	$V_{DS}=15V$ $V_{GS}=0V$ $f=1.0MHz$	C_{iss}	-	3420	-	pF
Output Capacitance		C_{oss}	-	1916	-	
Reverse Transfer Capacitance		C_{rss}	-	196	-	
Continuous Source Current ^{1,6}	$V_G=V_D=0V, \text{Force Current}$	I_S	-	-	100	A
Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	V_{SD}	-	-	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\cong 300\mu s$, duty cycle $\cong 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=55A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.
- 6.Package limitation current is 85A.

Ratings and Characteristic Curves

Typical Characteristics

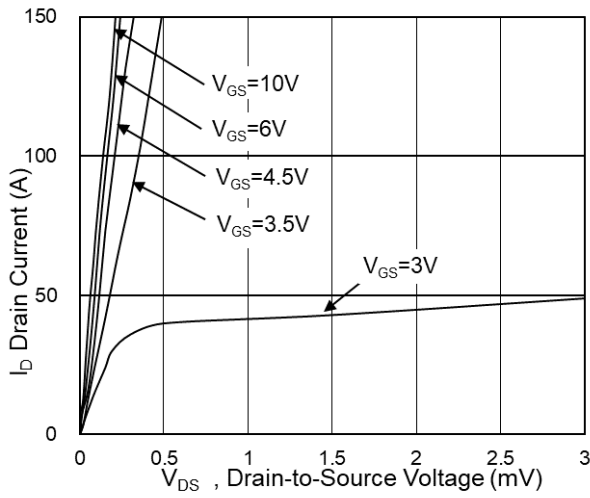


Fig.1 Typical Output Characteristics

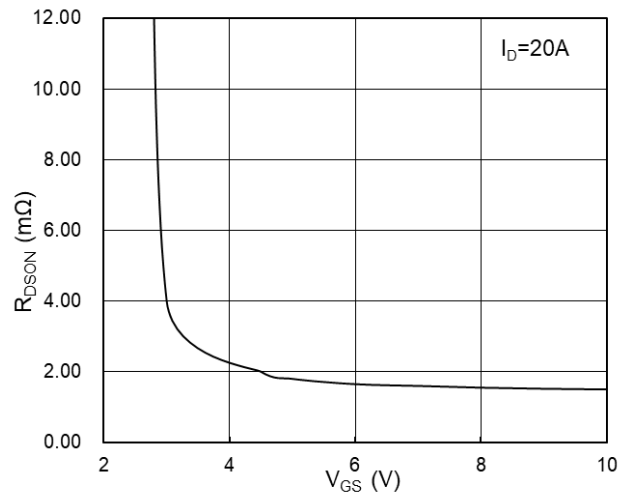


Fig.2 On-Resistance vs G-S Voltage

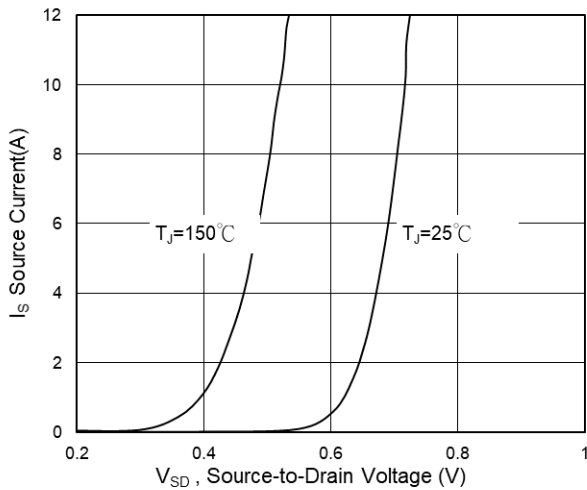


Fig.3 Source Drain Forward Characteristics

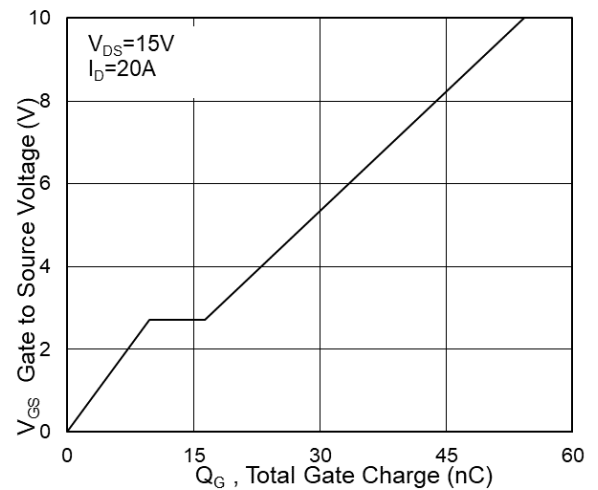


Fig.4 Gate-Charge Characteristics

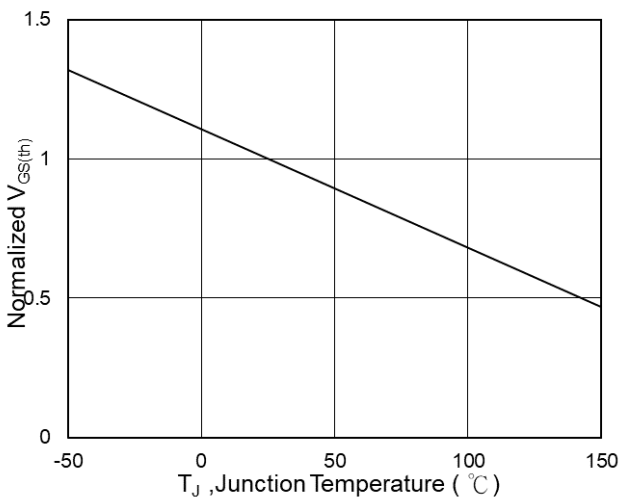


Fig.5 Normalized $V_{GS(th)}$ vs T_J

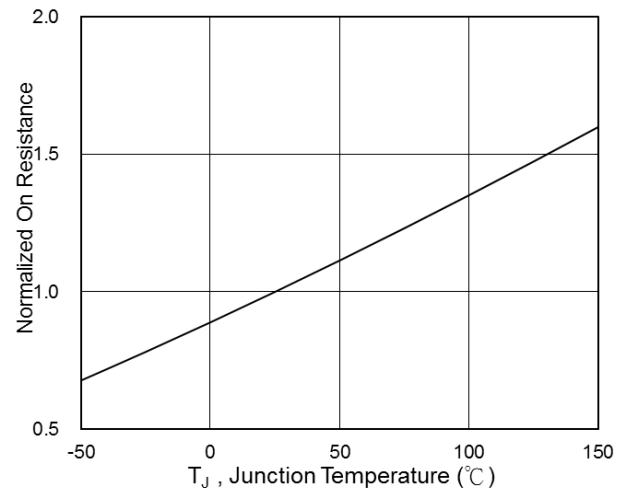


Fig.6 Normalized $R_{DS(ON)}$ vs T_J

Ratings and Characteristic Curves

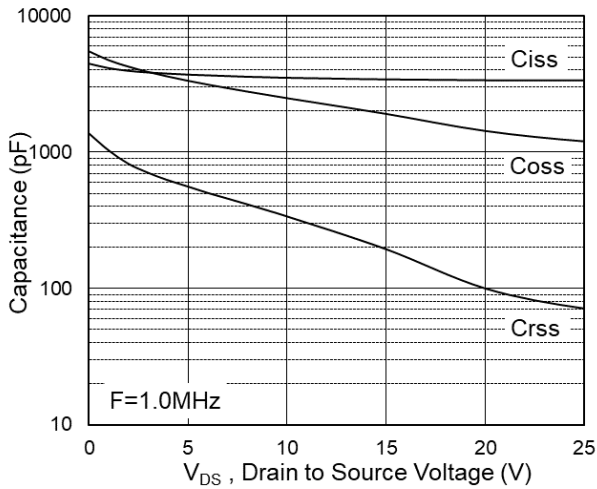


Fig.7 Capacitance

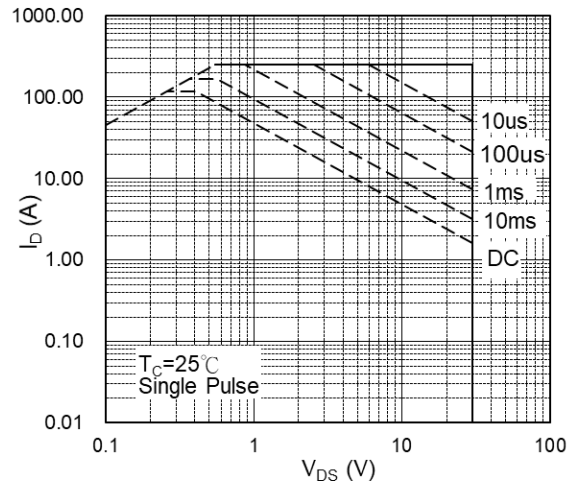


Fig.8 Safe Operating Area

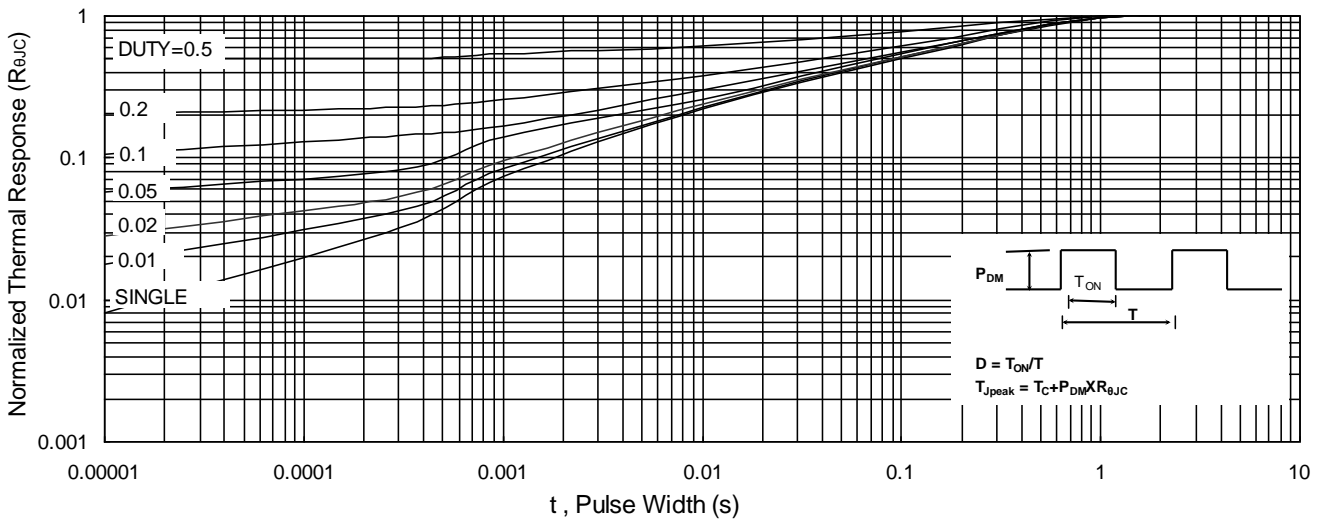


Fig.9 Normalized Maximum Transient Thermal Impedance

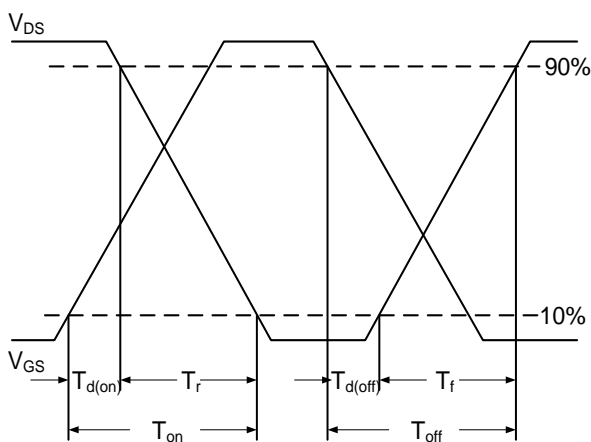


Fig.10 Switching Time Waveform

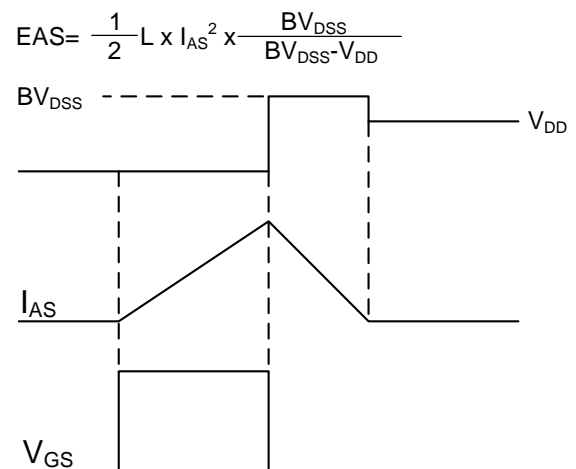
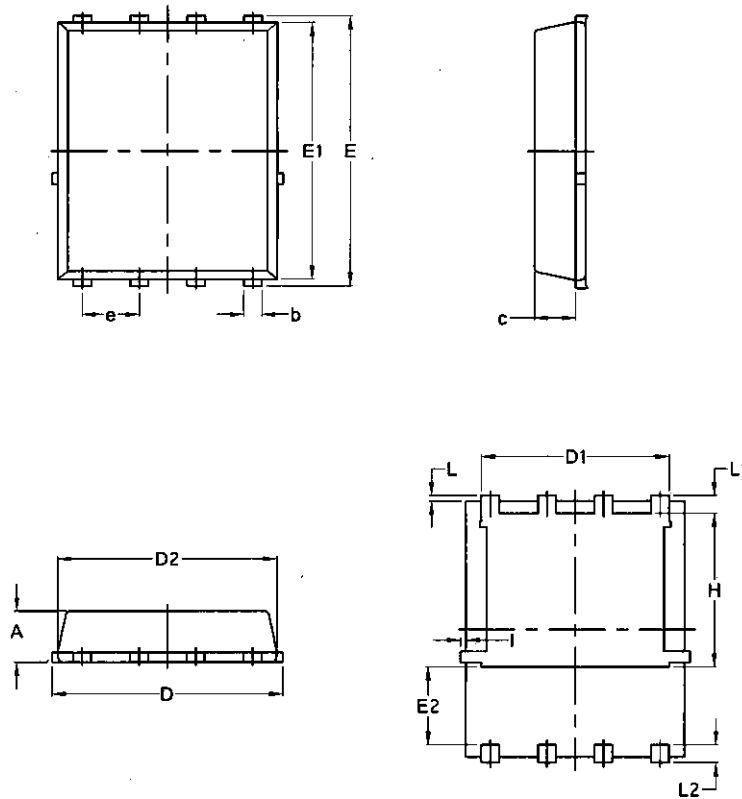


Fig.11 Unclamped Inductive Switching Waveform

PDFN5*6-8L



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070